





500V NPN HIGH VOLTAGE TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

Feature

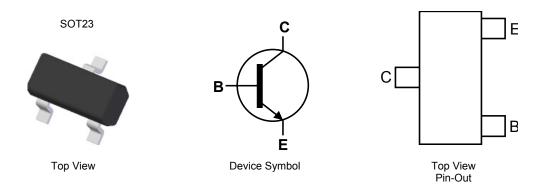
- BV_{CEV} > 500V
- BV_{ECV} > 6V reverse blocking
- I_C = 150mA high Continuous Collector Current
- I_{CM} Up to 500mA Peak Pulse Current
- 625mW Power Dissipation
- Low Saturation Voltage <-90mV @ 50mA
- Excellent h_{FE} Characteristics Up To 120mA
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (approximate)

Applications

- Automotive
- Off-line switching applications
- RCD circuits
- · PFC disable switch in PSU
- Emergency lighting
- Piezo actuators
- Telecom protected line switching



Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT459QTA	Automotive	459	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information







Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	500	V
Collector-Emitter Voltage	V _{CEV}	500	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EBO}	7	V
Emitter-Collector Voltage	V _{ECV}	6	V
Continuous Collector Current	I _C	150	mA
Peak Pulse Current	I _{CM}	500	mA
Base Current	I _B	200	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	$R_{ heta JL}$	194	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

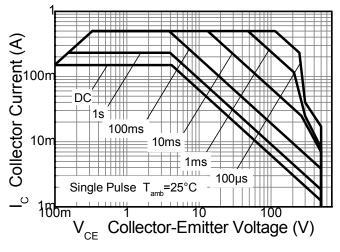
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

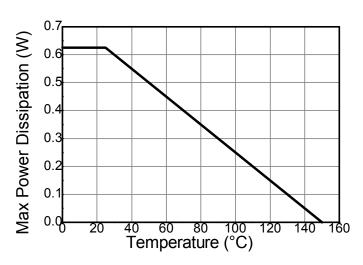
Notes:

- 6. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note 6, except the device is measured at $t \le 5$ sec.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



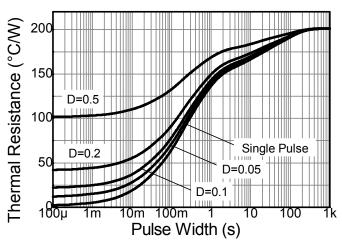
Thermal Characteristics and Derating Information

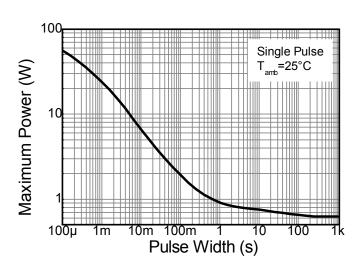




Safe Operating Area

Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation





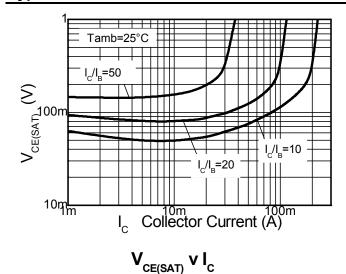
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

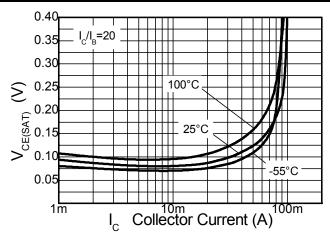
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	500	700	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV_CEV	500	700	_	V	$I_C = 10\mu A; 0.3V > V_{BE} > -1V$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	450	500	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.1	_	V	I _E = 100μA
Emitter-Base Breakdown Voltage (Reverse Blocking)	BV_{ECV}	6	8.1	_	V	$I_C = 1\mu A; 0.3V > V_{BC} > -6V$
Collector Cutoff Current	I _{CBO}	_	<10	100	nA	V _{CB} = 450V
Emitter Cutoff Current	I _{EBO}	_	<10	100	nA	V _{EB} = 5.6V
Collector Emitter Cutoff Current	I _{CES}	_	<10	100	nA	V _{CE} = 450V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	50	120	_	_	I _C = 30mA, V _{CE} = 10V
Static Folward Current Transfer Ratio (Note 10)		_	70	_		I _C = 50mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	60	75	mV	$I_C = 20$ mA, $I_B = 2$ mA
Concetor-Enritter Cataration Voltage (Note 10)	V CE(sat)	_	70	90	mV	$I_C = 50$ mA, $I_B = 6$ mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	0.71	0.9	V	I _C = 50mA, V _{CE} = 10V
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	_	0.76	0.9	V	$I_C = 50$ mA, $I_B = 5$ mA
Output Capacitance	C_{obo}	_	_	5	pF	$V_{CB} = 20V$, $f = 1MHz$
Transition Frequency	f _T	50	_	_	MHz	V_{CE} = 20V, I_{C} = 10mA, f = 20MHz
Turn-On Time	t _{on}	_	113	_	ns	$V_C = 100V, I_C = 50mA$
Turn-Off Time	t _{off}	_	3450	_	ns	$I_{B1} = 5mA$, $I_{B2} = -10mA$

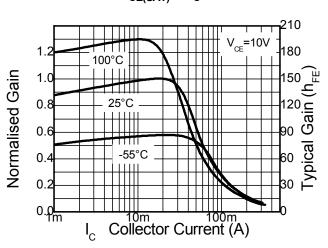
Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

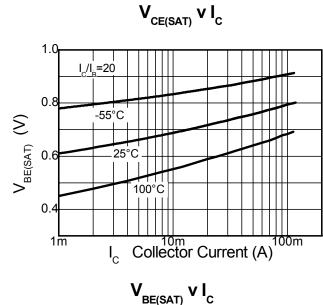


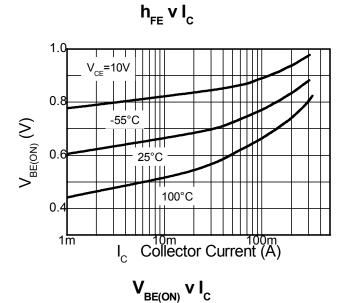
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







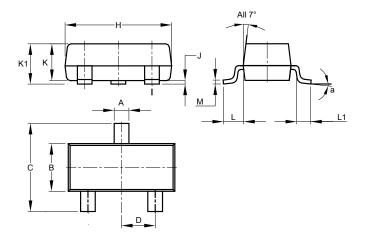






Package Outline Dimensions

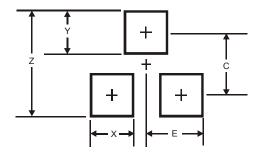
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45 0.61 0.5				
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	a 8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Υ	0.9		
С	2.0		
Е	1.35		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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